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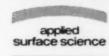
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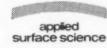
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Silica Silica

Silicides

Silicon Silicon carbide

Silicon nitride

Silicon oxide Silver

Solar cells

Sputter deposition

Sputtering

Steel

Strontium

Sulphides

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Catalysis by Metals and Alloys

By V. Ponec and G.C. Bond

Studies in Surface Science and Catalysis, Volume 95

The theoretical basis of chemisorption and catalysis by metals and alloys, and their use in a range of model and industrially significant catalysed processes are described in this book.

Model, as well as industrially used reactions catalyzed by alloys are reviewed, among them the Fischer-Tropsch synthesis, reactions of alkanes ('reforming'reactions), oxidations, hydro-/dehydrogenation, decomposition of methanoic acid, deuterium exchange reactions (H2. hydrocarbons) and to a lesser extent some others. This review on catalytic reactions, with results from the available information, is introduced in two chapters which summarize the definition, the physical meaning and the role of such factors as ligand (electronic structure), ensemble size (geometrical) and ensemble composition effects. The assessment of the roles of these individual factors reguires the knowledge of several physical techniques and a proper evaluation of the results obtained by them. An introduction to this field of physics forms the content of the introductory chapters of this book.

A long period (1968-1994) of intensive research into catalysis by alloys has just been concluded so that reliable conclusions can be drawn concerning the roles of ligand, geometric and compositional effects. Particular attention is paid to the connection between chemisorption and catalytic phenomena, and their dependence on the structure of the surface as revealed by current techniques of solid-state physics is highlighted.

Scientists in related fields, such as electrochemistry, solid state chemistry, materials science, corrosion, tribology and other fields of applied surface science, organic synthesis and general inorganic chemistry should find the information contained in this book of interest in their work.

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